

20CTH03PbF 20CTH03FPPbF

Hyperfast Rectifier

Features

- · Hyperfast Recovery Time
- Low Forward Voltage Drop
- Low Leakage Current
- 175°C Operating Junction Temperature Lead-Free ("PbF" suffix)

t_{rr} = 35ns max. $I_{F(AV)} = 20Amp$

 $V_{R} = 300V$

Description/ Applications

International Rectifier's 300V series are the state of the art Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and Hyperfast recovery time.

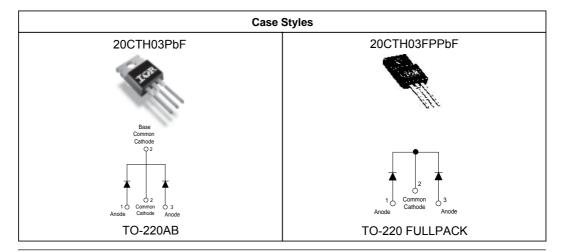
The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

Absolute Maximum Ratings

	Parameters		Max	Units
V _{RRM}	Peak Repetitive Reverse Voltage		300	V
I _{F(AV)}	Average Rectified Forward Current	@ T _C = 160°C Per Diode	10	А
	@ T _C = 135°C (FULLPACK)	Per Diode		
		Per Device	20	
I _{FSM}	Non Repetitive Peak Surge Current	120		
T _J , T _{STG}	Operating Junction and Storage Te	- 65 to 175	°C	



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	· · · · · · · · · · · · · · · · · · ·							
	Parameters	Min	Тур	Max	Units	Test Conditions		
V_{BR}, V_{r}	Breakdown Voltage, Blocking Voltage	300	-	-	V	I _R = 100μA		
V _F	Forward Voltage	-	1.05	1.25	٧	I _F = 10A, T _J = 25°C		
		-	0.85	0.95	V	I _F = 10A, T _J = 125°C		
I _R	Reverse Leakage Current	-	-	20	μA	V _R = V _R Rated		
		-	6	200	μA	$T_J = 125^{\circ}C$, $V_R = V_R$ Rated		
Ст	Junction Capacitance	-	30	-	pF	V _R = 300V		
L _S	Series Inductance	-	8	-	nH	Measured lead to lead 5mm from package body		

Dynamic Recovery Characteristics @ T_C = 25°C (unless otherwise specified)

	Parameters	Min	Тур	Max	Units	Test Conditions		
t _{rr}	Reverse Recovery Time	-	-	35	ns	$I_F = 1A$, $di_F/dt = 50A/\mu s$, $V_R = 30V$		
		-	-	30		$I_F = 1A$, di_F/dt	_F /dt = 100A/µs, V _R = 30V	
		-	31	-		T _J = 25°C		
		-	42	-		T _J = 125°C	I _F = 10A	
I _{RRM}	Peak Recovery Current	-	2.4	-	Α	$T_J = 25^{\circ}C$	di _F /dt = 200A/μs	
		-	5.6	-		T _J = 125°C	V _R = 200V	
Qrr	Reverse Recovery Charge	-	36	-	nC	T _J = 25°C		
		-	120	-		T _J = 125°C		

Thermal - Mechanical Characteristics

	Parameters		Min	Тур	Max	Units
TJ	Max. Junction Temper	-	-	175	°C	
T _{Stg}	Max. Storage Temper	- 65	-	175		
R _{thJC} ①	Thermal Resistance,	Per Diode	-	-	1.5	°C/W
	Junction to Case	Fullpack (Per Diode)	1	-	3.9	
	Device Marking		20CTH03			Case Style TO-220
			20CTH03FP			Case Style Fullpack

 $[\]ensuremath{\mathbb{O}}$ Mounting Surface, Flat, Smooth and Greased

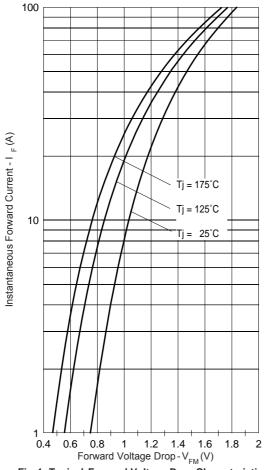


Fig. 1-Typical Forward Voltage Drop Characteristics

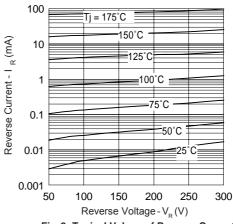


Fig. 2-Typical Values of Reverse Current Vs. Reverse Voltage

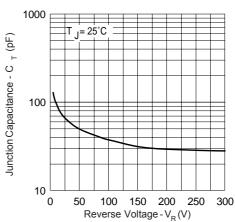


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

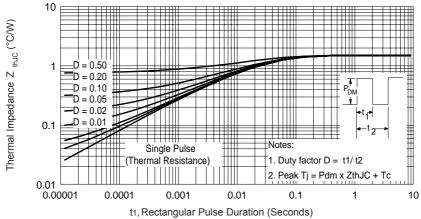


Fig. 4-Max. Thermal Impedance Z_{thJC} Characteristics

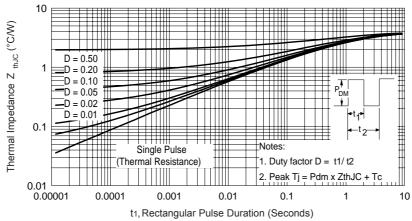


Fig. 5 - Max. Thermal Impedance Z_{thJC} Characteristics (FULLPACK)

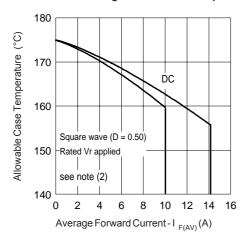


Fig. 6 - Max. Allowable Case Temperature Vs. Average Forward Current

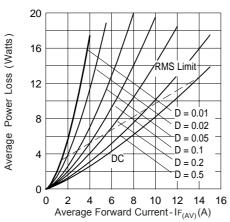


Fig. 8-Forward Power Loss Characteristics

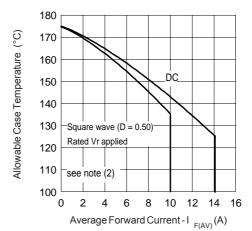


Fig. 7 - Max. Allowable Case Temperature Vs. Average Forward Current (FULLPACK)

(2) Formula used: $T_C = T_J - (Pd + Pd_{REV})xR_{thJC}$; $Pd = Forward Power Loss = I_{F(AV)}xV_{FM} @ (I_{F(AV)}/D)$ (see Fig. 8); $Pd_{REV} = Inverse Power Loss = V_{R1}xI_R(1-D)$; $I_R @ V_{R1} = rated V_R$

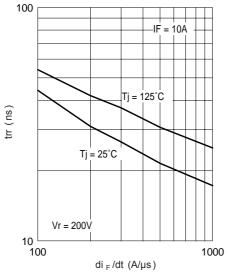


Fig. 9-Typical Reverse Recovery vs. di _F/dt

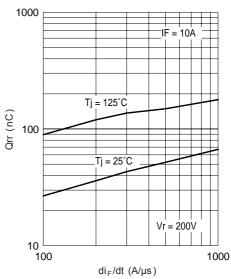


Fig. 10 - Typical Stored Charge vs. di_F/dt

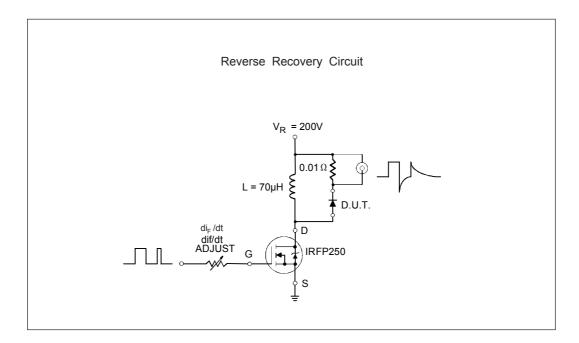


Fig. 11- Reverse Recovery Parameter Test Circuit

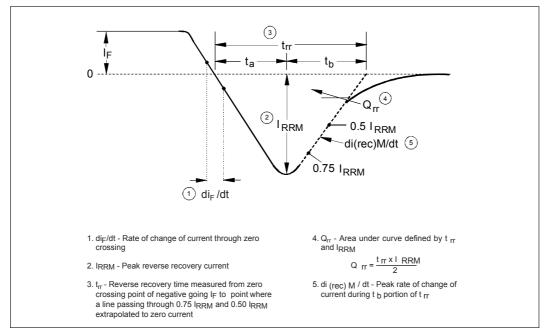
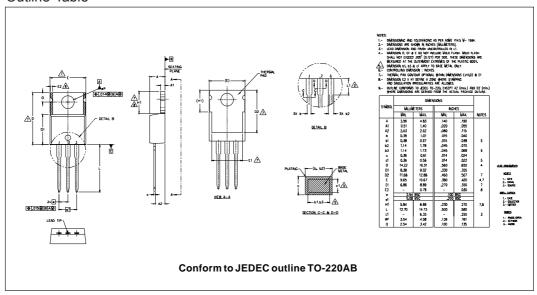
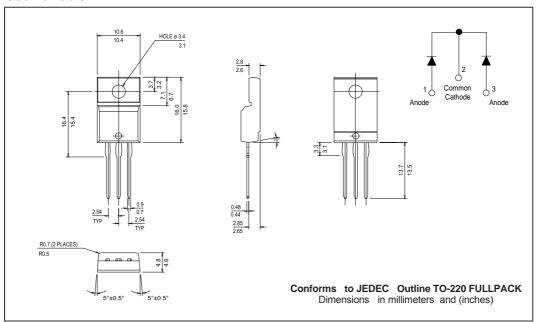


Fig. 13 - Reverse Recovery Waveform and Definitions

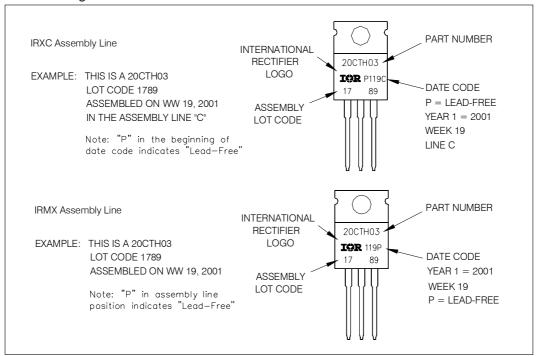
Outline Table



Outline Table

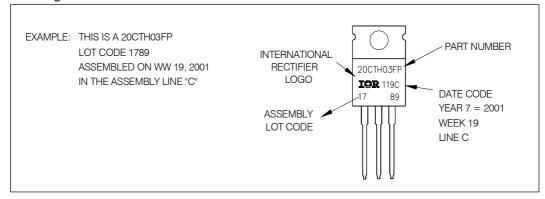


Part Marking Information

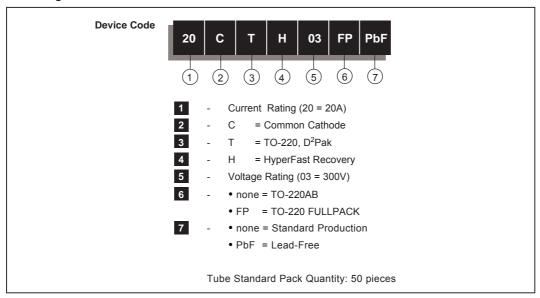


Bulletin PD-20893 rev. A 10/06

Marking Information



Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for AEC Q1O1 Level and Lead-Free. Qualification Standards can be found on IR's Web site.



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7309
Visit us at www.irf.com for sales contact information. 10/06